

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)		ATTY. DOCKET NO. 57810-098		SERIAL NO. 			
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U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number <small>Number-Kind Code² (if known)</small>	Publication Date <small>MM-DD-YYYY</small>	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document <small>Country Code¹-Number²-Kind Code³ (if known)</small>	Publication Date <small>MM-DD-YYYY</small>	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. <div style="border: 1px solid black; padding: 5px; margin: 5px 0;"> Seigo KISHINO, "Basis of Semiconductor Device", Published by Ohmsha, Ltd., April 26, 1985 "Sub-micron Device I", pp. 49-54, July 84, 1987 </div>					
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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.